

FPN560 FPN560A



NPN Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 3.0 A continuous. Sourced from Process NA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	3.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		FPN560 / FPN560A		
P _D	Total Device Dissipation	1.0	W	
R _{θJC}	Thermal Resistance, Junction to Case	50	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W	

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

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Min

(continued)

Units

Max

Electrical Characteristics	TA = 25°C unless otherwise noted
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Parameter

OFF CHARACTERISTICS					
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA
		$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 100^{\circ}\text{C}$		10	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		100	nA

Test Conditions

ON CHARACTERISTICS*

Symbol

h _{FE}	DC Current Gain	$\begin{split} &I_{C} = 100 \text{ mA}, \text{ V}_{CE} = 2.0 \text{ V} \\ &I_{C} = 500 \text{ mA}, \text{ V}_{CE} = 2.0 \text{ V} \\ &I_{C} = 1.0 \text{ A}, \text{ V}_{CE} = 2.0 \text{ V} \\ &I_{C} = 2.0 \text{ A}, \text{ V}_{CE} = 2.0 \text{ V} \end{split}$	560 560A	70 100 250 80 40	300 550	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 2.0 \text{ A}, I_B = 200 \text{ mA}$	560 560A		300 350 300	mV mV mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$			1.25	V
V _{BE(on)}	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$			1.0	V

SMALL SIGNAL CHARACTERISTICS

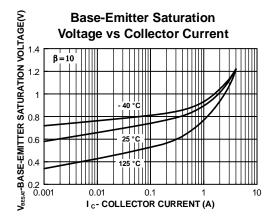
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		30	pF
F _T	Transition Frequency	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 100 MHz	75		MHz

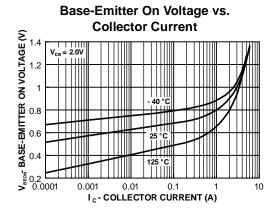
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

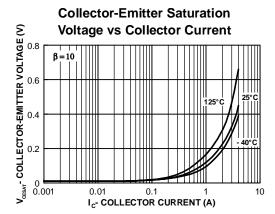
NPN Low Saturation Transistor

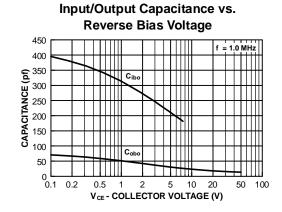
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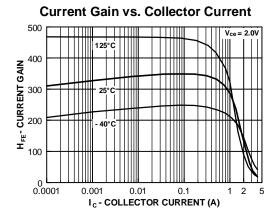
Typical Characteristics

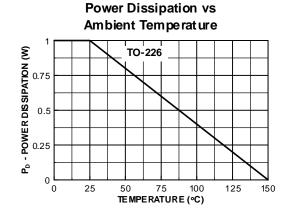












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